

IN THE CLAIMS

Claims 1-43 (Canceled).

44 (Currently Amended). A method comprising:
forming an electrically insulating protective layer over a conductive lower electrode of a phase change memory;
forming a pore over said insulating protective layer;
etching through said pore to open up said protective layer;
forming a chalcogenide in said pore touching said lower electrode; and
depositing forming the lower electrode and covering the lower electrode with a protective layer in the same chamber without venting back to the atmosphere.

Claims 45-47 (Canceled).

48 (Previously Presented). The method of claim 44 including forming the protective layer of an insulator.

49 (Previously Presented). The method of claim 48 including forming the protective layer of a material in the form of silicon nitride.

50 (Previously Presented). The method of claim 49 including forming the silicon nitride in the form of Si_3N_4 .